2SK3217-01MR

FUJI POWER MOS-FET

N-CHANNEL SILICON POWER MOS-FET

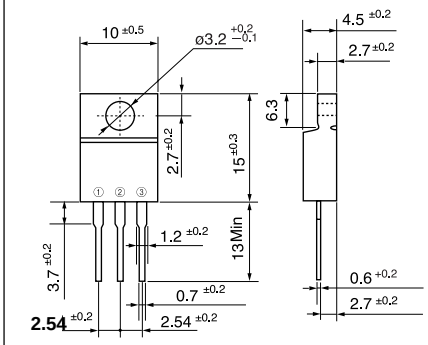
■ Features

High speed switching
Low on-resistance
No secondary breadown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

TO-220F15



1. Gate
2. Drain
3. Source

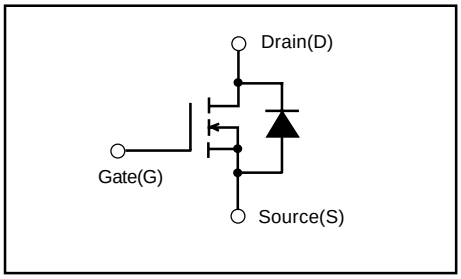
■ Maximum ratings and characteristic Absolute maximum ratings

● **(Tc=25°C unless otherwise specified)**

Item		Symbol	Rating	Unit
Drain-source voltage		V_{DS}	100	V
Continuous drain current		I_D	±50	A
Pulsed drain current		$I_{D(puls)}$	±200	A
Gate-source voltage		V_{GS}	±30	V
Maximum Avalanche Energy		E_{AV}*1	464	mJ
Max. power dissipation	Ta=25°C	P_D	2.0	W
	Tc=25°C	P_D	70	W
Operating and storage temperature range		T_{ch}	+150	℃
		T_{stg}	-55 to +150	℃

*1 L=298μH, Vcc=24V

■ Equivalent circuit schematic



● **Electrical characteristics (T_C =25°C unless otherwise specified)**

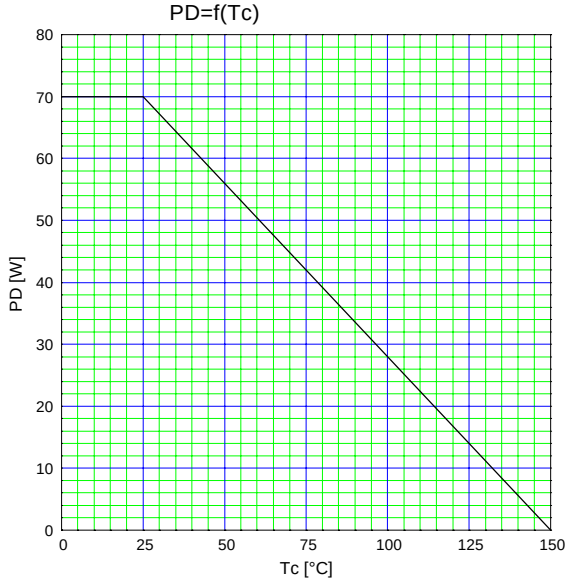
Item	Symbol	Test Conditions		Min.	Typ.	Max.	Units
Drain-source breakdown voltaget	$V_{(BR)DSS}$	I_D=1mA V_{GS}=0V		100			V
Gate threshold voltage	$V_{GS(th)}$	I_D=1mA V_{DS}=V_{GS}		2.5	3.0	3.5	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=100V V_{GS}=0V	Tch=25°C		1	100	μA
			Tch=125°C		0.1	0.5	mA
Gate-source leakage current	I_{GSS}	V_{GS}=±30V V_{DS}=0V			10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	I_D=25A V_{GS}=10V			20	25	mΩ
Forward transcondutance	g_{fs}	I_D=25A V_{DS}=25V		16.0	32.0		S
Input capacitance	C_{iss}	V_{DS}=25V			3200	4800	pF
Output capacitance	C_{oss}	V_{GS}=0V			760	1140	
Reverse transfer capacitance	C_{rss}	f=1MHz			230	345	
Turn-on time t_{on}	$t_{d(on)}$	V_{CC}=48V I_D=50A			23	35	ns
	t_r	V_{GS}=10V			130	195	
Turn-off time t_{off}	$t_{d(off)}$	R_{GS}=10Ω			110	165	
	t_f				65	100	
Avalanche capability	I_{AV}	L=100μH Tch=25°C		50			A
Diode forward on-voltage	V_{SD}	I_F=50A V_{GS}=0V Tch=25°C			0.97	1.46	V
Reverse recovery time	t_{rr}	I_F=50A V_{GS}=0V			150		ns
Reverse recovery charge	Q_{rr}	-di/dt=100A/μs Tch=25°C			0.80		μC

● **Thermalcharacteristics**

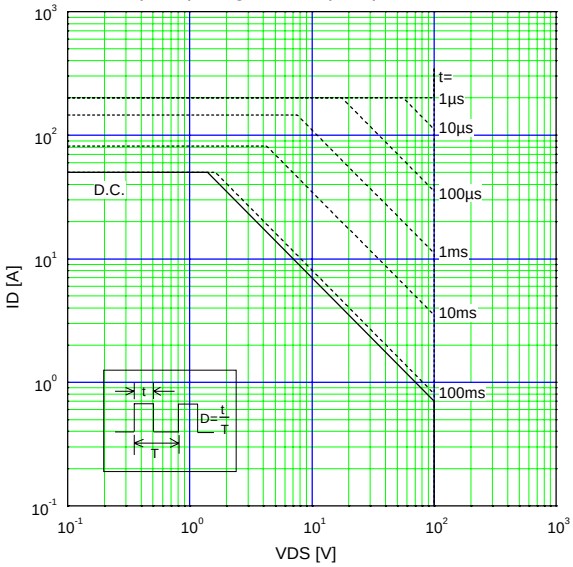
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			1.79	°C/W
	$R_{th(ch-a)}$	channel to ambient			62.5	°C/W

Characteristics

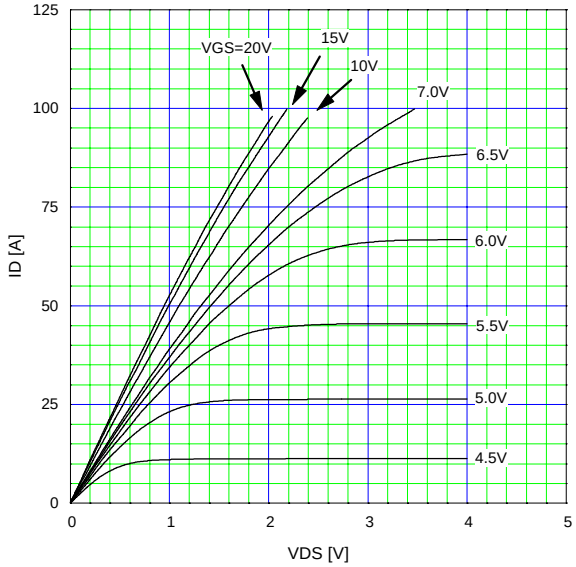
Power Dissipation
PD=f(Tc)



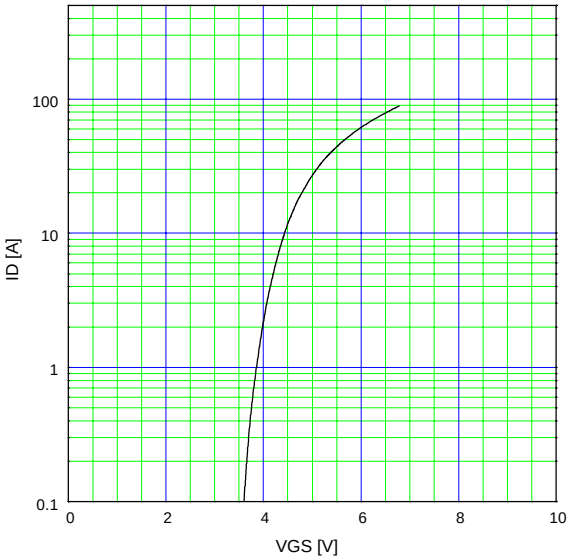
Safe operating area
ID=f(VDS):Single Pulse(D=0),Tc=25°C



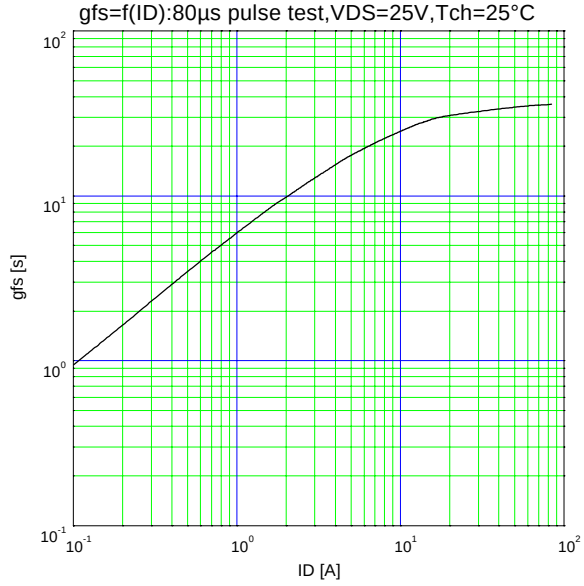
Typical output characteristics
ID=f(VDS):80µs pulse test,Tc=25°C



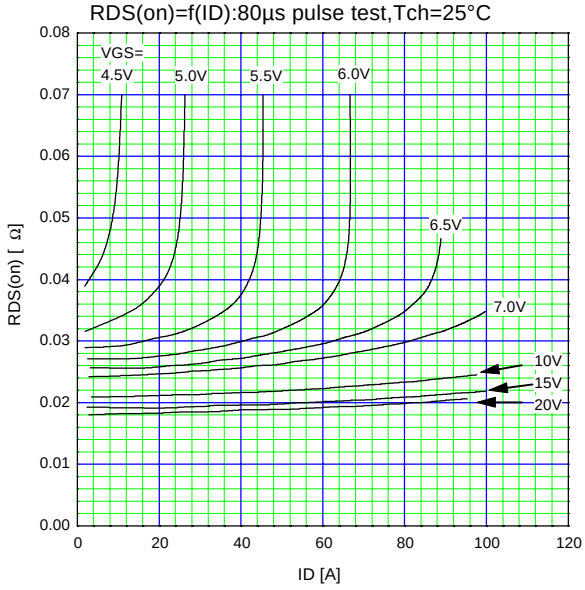
Typical transfer characteristics
ID=f(VGS):80µs pulse test,VDS=25V,Tch=25°C



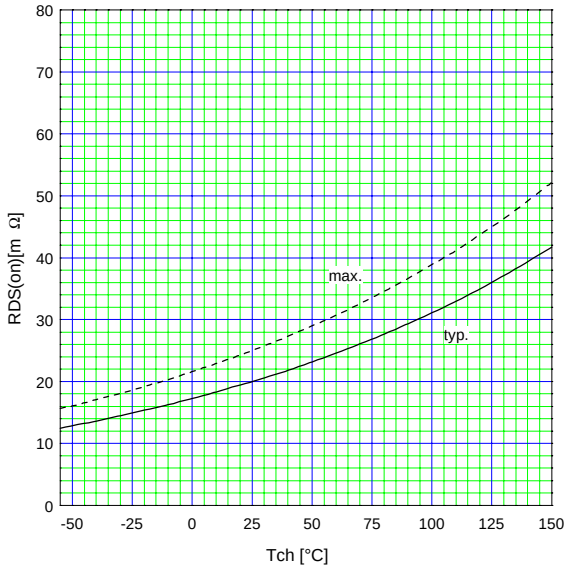
Typical forward transconductance
gfs=f(ID):80µs pulse test,VDS=25V,Tch=25°C



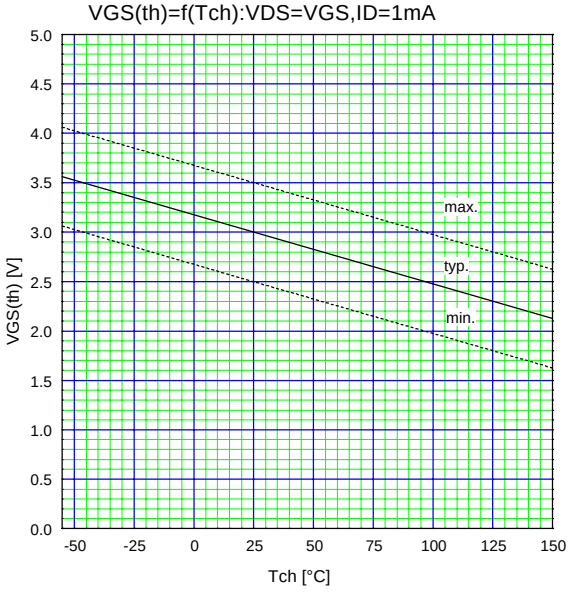
Typical Drain-Source on-State Resistance
RDS(on)=f(ID):80µs pulse test,Tch=25°C



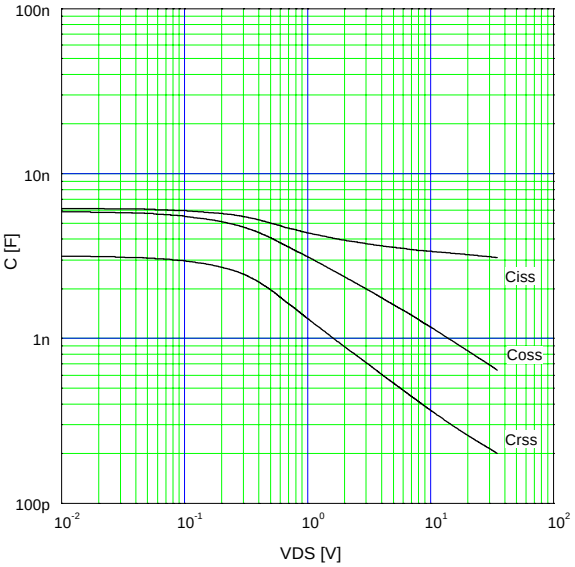
Drain-source on-state resistance
RDS(on)=f(Tch):ID=25A,VGS=10V



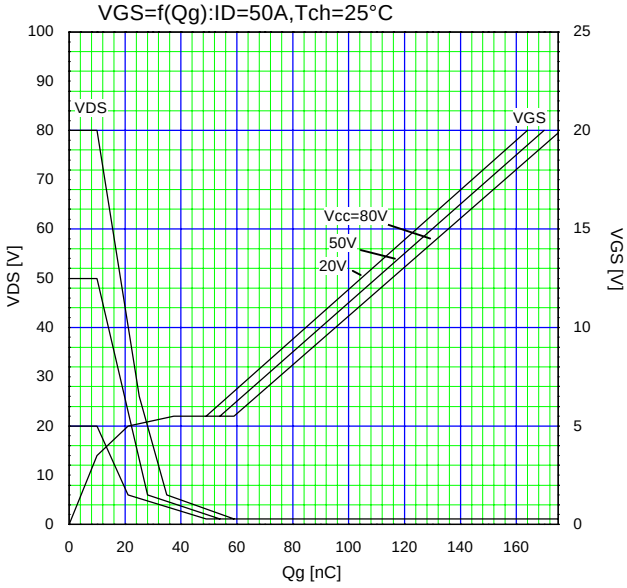
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch):VDS=VGS,ID=1mA



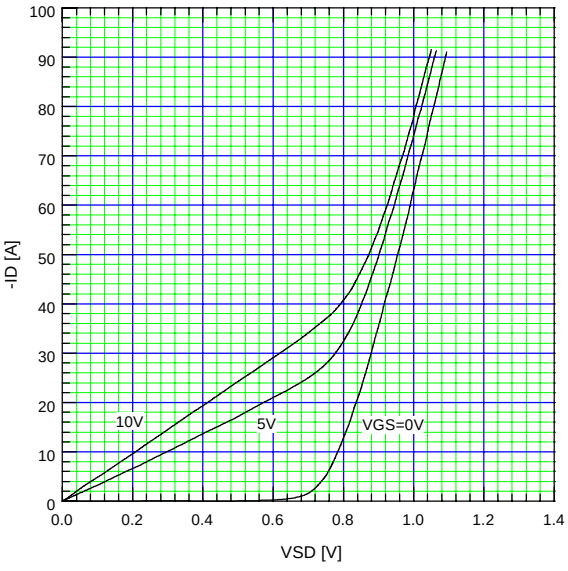
Typical capacitances
C=f(VDS):VGS=0V,f=1MHz



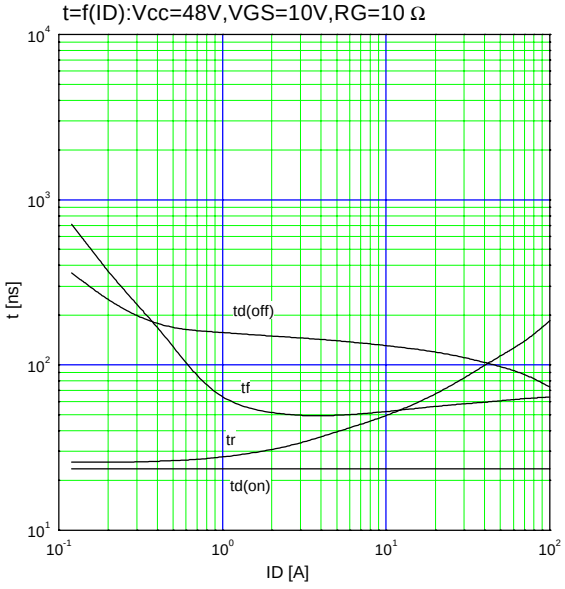
Typical Gate Charge Characteristics
VGS=f(Qg):ID=50A,Tch=25°C



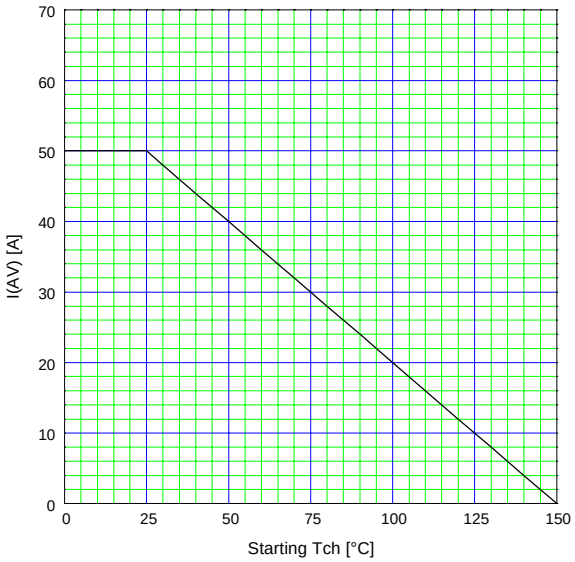
Typical Forward Characteristics of Reverse Diode
-ID=f(VSD):80µs pulse test,Tch=25°C



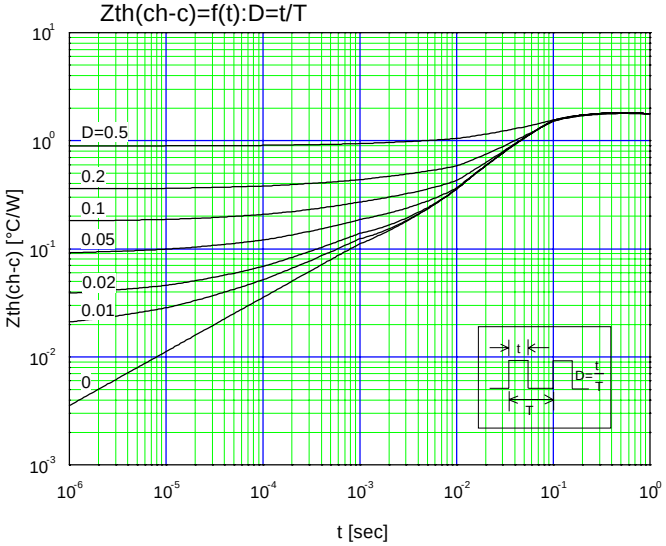
Typical Switching Characteristics vs. ID
t=f(ID):Vcc=48V,VGS=10V,RG=10 Ω



Maximum Avalanche Current vs. starting Tch
I(AV)=f(starting Tch),Non Repetitive



Transient Thermal Impedance
Zth(ch-c)=f(t):D=t/T



Maximum Avalanche energy vs. starting Tch
Eas=f(starting Tch):Vcc=24V,I_{AV}<=50A,Non-Repetitive